

IGBT³ Chip

FEATURES:

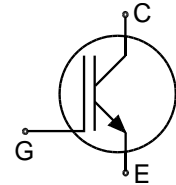
- 600V Trench & Field Stop technology
- low $V_{CE(sat)}$
- low turn-off losses
- short tail current
- positive temperature coefficient
- easy paralleling

This chip is used for:

- power module
- discrete components

Applications:

- drives



Chip Type	V_{CE}	I_C	Die Size	Package
SIGC28T60SE	600V	50A	6.57 x 4.2 mm ²	sawn on foil

Mechanical Parameters

Raster size	6.57 x 4.2	mm ²
Emitter pad size (incl. gate pad)	2.166 x 3.401 2.432 x 3.401	
Gate pad size	0.817 x 1.52	
Area total	27.6	
Thickness	70	µm
Wafer size	200	mm
Max.possible chips per wafer	974	
Passivation frontside	Photoimide	
Pad metal	3200 nm AlSiCu	
Backside metal	Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	Electrically conductive glue or solder	
Wire bond	Al, <500µm	
Reject ink dot size	Ø 0.65mm ; max 1.2mm	
Recommended storage environment	Store in original container, in dry nitrogen, in dark environment, < 6 month at an ambient temperature of 23°C	

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter voltage, $T_{vj}=25\text{ °C}$	V_{CE}	600	V
DC collector current, limited by $T_{vj\text{ max}}$	I_C	1)	A
Pulsed collector current, t_p limited by $T_{vj\text{ max}}$	$I_{C,puls}$	150	A
Gate emitter voltage	V_{GE}	± 20	V
Junction temperature range	T_{vj}	-40 ... +175	°C
Operating junction temperature	T_{vj}	-40...+150	°C
Short circuit data ²⁾ $V_{GE} = 15V, V_{CC} = 360V, T_{vj} = 150\text{ °C}$	t_{SC}	6	μs
Reverse bias safe operating area ²⁾ (RBSOA)	$I_{C,max} = 100A, V_{CE,max} = 600V$ $T_{vj} \leq 150\text{ °C}$		

1) depending on thermal properties of assembly

2) not subject to production test - verified by design/characterization

Static Characteristics (tested on wafer), $T_{vj}=25\text{ °C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-Emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=4\text{ mA}$	600			V
Collector-Emitter saturation voltage	V_{CEsat}	$V_{GE}=15V, I_C=50A$	1.05	1.45	1.85	
Gate-Emitter threshold voltage	$V_{GE(th)}$	$I_C=0.8mA, V_{GE}=V_{CE}$	5.0	5.8	6.5	
Zero gate voltage collector current	I_{CES}	$V_{CE}=600V, V_{GE}=0V$			2.6	μA
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V$			600	nA
Integrated gate resistor	r_G			--		Ω

Dynamic Characteristics (not subject to production test - verified by design / characterization),

$T_{vj}=25\text{ °C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	C_{ies}	$V_{CE}=25V,$ $V_{GE}=0V,$ $f=1\text{ MHz}$		3140		pF
Output capacitance	C_{oes}			200		
Reverse transfer capacitance	C_{res}			93		



SIGC28T60SE

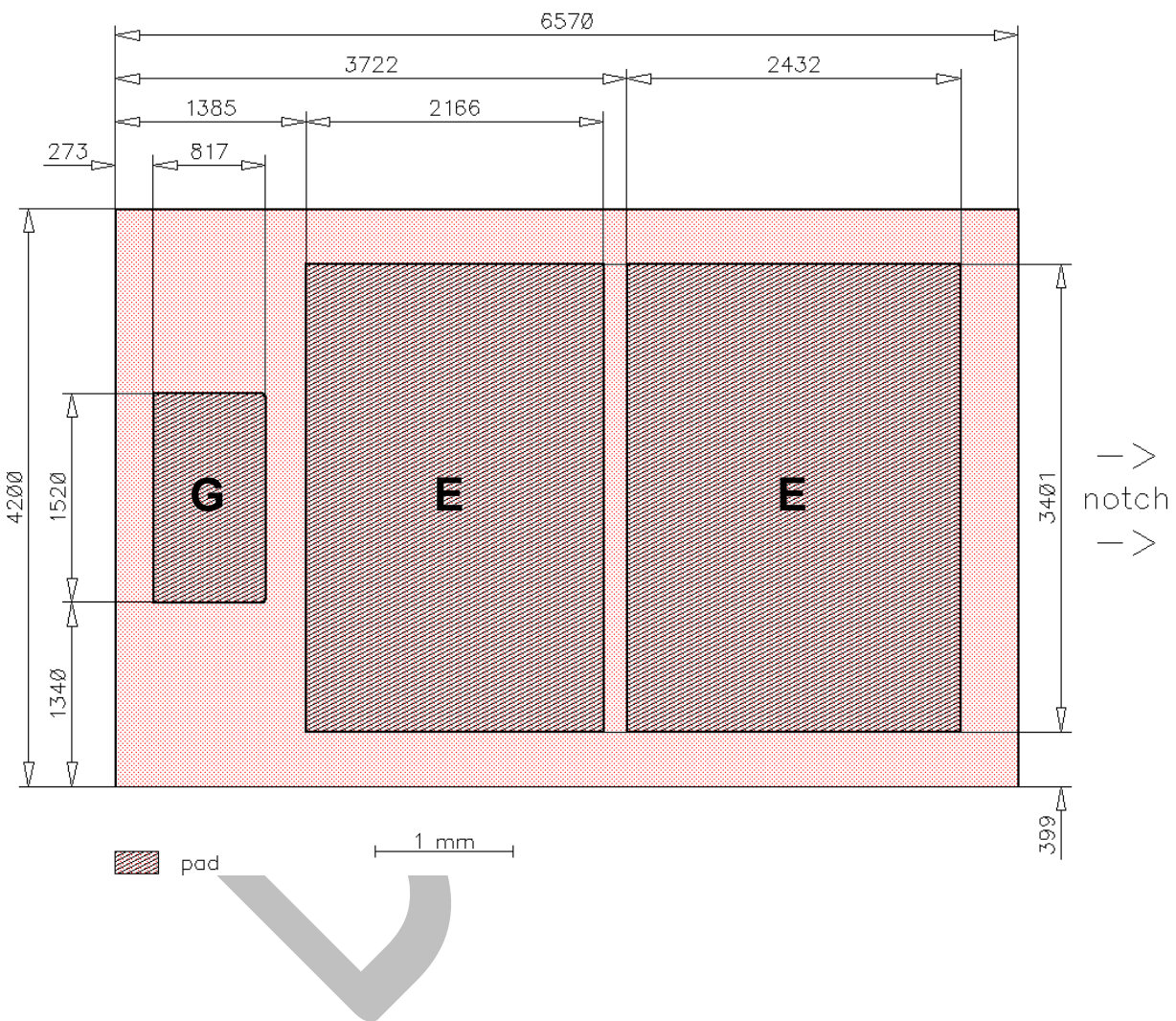
Further Electrical Characteristic

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

DRAFT

Chip Drawing

Die-Size 6570 um x 4200 um





SIGC28T60SE

Bare Die Product Specifics

Test coverage at wafer level cannot cover all application conditions. Therefore it is recommended to test all characteristics which are relevant for the application at package level, including RBSOA and SCSOA.

Description

AQL 0,65 for visual inspection according to failure catalogue

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Revision History

Version	Subjects (major changes since last revision)	Date
2.0	Wafer diameter change to 200 mm	07.07.2010
2.1	Update of chip drawing and disclaimers	30.03.2015

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